

REMARKS

In response to the Office action identified above,
5 please accept the following remarks.

**1. Response to the rejection of claim 1 under 35 U.S.C.
102(e):**

10 Claim 1 is rejected under 35 U.S.C. 102(e) as being
anticipated by Wang (US 6,707,129).

Wang describes a method of forming a fuse structure
integrated wire bonding comprising: forming one
15 conductive layer on a first and second area of the
substrate (figs. 1 and 3); forming a first dielectric
layer on the surface of the substrate that covers each
conductive layer (fig. 4); removing portions of the
conductive layer in the first area until the remaining
20 conductive layer in the first area is of a predetermined
thickness (fig. 2); and removing portions of the first
dielectric layer in the first area and in the second
area until reaching the top surface of the conductive
layer (fig. 5).

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Response:

First, claim 6 is merged into claim 1 to overcome
this rejection, and claim 6 is therefore canceled.

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Second, the Applicant intends to point out the
difference between the amended claim 1 of the present

application and Wang's disclosure. The amended claim 1 of the present application is repeated below:

Claim 1 (Currently amended): A method of making a
5 conductive layer on a substrate, a surface of the substrate comprising a first area and a second area, the method comprising:

forming at least one conductive layer on the first area and on the second area, respectively;

10 forming a first dielectric layer on the surface of the substrate that covers each conductive layer;

**removing portions of the first dielectric layer to define at least one first opening in the first dielectric layer, and using the first dielectric layer as a mask
15 to remove portions of the conductive layer underneath the first opening until the remaining conductive layer in the first area is of a predetermined thickness; and**

removing portions of the first dielectric layer in the second area until reaching the top surface of the
20 conductive layer.

As disclosed in the amended claim 1, the first opening is formed in the first dielectric layer, and the first dielectric layer is used as a mask to remove portions
25 of the conductive layer underneath the first opening. However, Wang removes portions of the conductive layer 104 prior to the formation of the first opening 112b in the first dielectric layer 110 (FIG. 2 and FIG. 5). Since Wang forms the first opening 112b in the first
30 dielectric layer 110 after etching the conductive layer 104, it is believed that the first dielectric layer 110 taught by Wang cannot be used as a mask to remove

portions of the conductive layer 104 underneath the first opening 112b. In addition, Wang specifically teaches to use "a first photoresist layer" as a mask to etch portions of the conductive layer 104 (Col. 3, lines 23-33), and use "a third photoresist layer" to form the first opening 112b in the first dielectric layer 110 (Col. 4, lines 1-9). From the aforementioned reasons, the Applicant believes that the amended claim 1 of the present application is absolutely different from Wang's disclosure. Reconsideration of the amended claim 1 is politely requested.

2. Response to the rejection of claims 3-5 and 10-13 under 35 U.S.C. 102(e):

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Referring to claims 3-5, 11, the surface of the substrate further comprises at least a conductive disposed in a second dielectric layer wherein the conductive layer comprises Cu, Al (col. 3, line 3-15).

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Referring to claim 10, the conductive layer thickness is 10000-20000 angstrom and the predetermined thickness is about 5000 angstrom (col. 3, line 14-16, line 35, 36).

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Referring to claim 12, the first area is fuse area and the conductive layer in the first area is a fuse, the second area is a pad area (claimed bonding pad area) and the conductive layer in the second area is a pad (claimed bonding pad) (col. 1, line 38-42; col. 3, line 41-50).

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Referring to claim 13, the metal conductors are also formed for interconnections (col. 1, line 24-27). This would read on claimed metal lines.

5 Response:

As claims 3-5 and 10-13 are dependent upon the amended claim 1, they should be allowed if the amended claim 1 is allowed. Reconsideration of claims 3-5 and 10-13 is therefore requested.

3. Response to the rejection of claim 2 under 35 U.S.C. 103(a):

Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wang as applied to claim 1 above, and further in view of admitted prior art.

Referring to claim 2, even though Wang is silent about the substrate is a silicon substrate. However, silicon has been known to any skilled in the art as the substrate to form a semiconductor device including a fuse and metal lines as shown in the admitted prior art in page 2 of the specification. Therefore, using a silicon substrate would be obvious to one skilled in the art with a reasonable expectation of success.

Response:

As claim 2 is dependent upon the amended claim 1, it should be allowed if the amended claim 1 is allowed. Reconsideration of claim 2 is therefore requested.

4. Objection over claims 7 and 8:

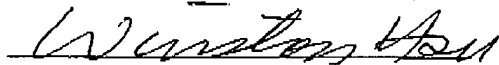
5 Claims 7, 8 are objected to as being dependent upon
a rejected base claim, but would be allowable if
rewritten in independent form including all of the
limitations of the base claim and any intervening
claims.

10 Response:

 As claims 7 and 8 are dependent on the amended claim
1, they should be allowed if the amended claim 1 is
allowed. Reconsideration of the objection over claims
15 7 and 8 is hereby requested.

Sincerely yours,

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communication and I will return your call promptly.)